What is claimed is:

1. An epoxy resin composition for semiconductor sealing comprising an epoxy resin, a phenol resin, an inorganic filler, a curing accelerator, and a carbon precursor having a specific electric resistivity in a semiconductor region of 1×10^2 ·cm or more but less than 1×10^7 ·cm as essential components, wherein the amounts of the inorganic filler and the carbon precursor in the epoxy resin composition are respectively 65-92 wt% and 0.1-5.0 wt%.

2. The epoxy resin composition for semiconductor sealing according to claim 1, wherein the carbon precursor has an H/C ratio by weight determined by elemental analysis of 2/97 to 4/93.

3. The epoxy resin composition for semiconductor sealing according to claim 1, wherein the carbon precursor is fine particles having an average particle diameter of 0.5-50 μm.

4. The epoxy resin composition for semiconductor sealing according to claim 1, wherein the carbon precursor is fine particles having an average particle diameter of 0.5-20 μm.

5. The epoxy resin composition for semiconductor sealing according to claim 1, wherein the carbon precursor has a specific electric resistivity of 1×10^4 ·cm or more but less

than 1×10^7 ·cm.

6. The epoxy resin composition for semiconductor sealing according to claim 1, wherein the amount of the inorganic filler in the total amount of the epoxy resin composition is 70-91 wt%.

7. The epoxy resin composition for semiconductor sealing according to claim 1, wherein the carbon precursor is produced by carbonizing a phenol resin at a calcination temperature of 600-650°C.

8. A semiconductor device comprising a semiconductor element sealed using the epoxy resin composition for semiconductor sealing according to any one of claims 1-7.